STD100N03L
STD100N03L-1

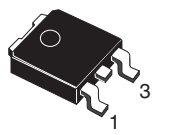
N-channel 30V - 0.0045Ω - 80A - DPAK - IPAK
Planar STripFET™ II Power MOSFET

General features

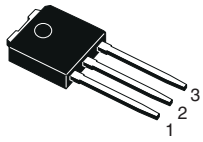
Type	V_{DSSS}	$R_{DS(on)}$	I_D	Pw
STD100N03L	30 V	<0.0055 Ω	80 A(1)	110 W
STD100N03L-1	30 V	<0.0055 Ω	80 A(1)	110 W

1. Current limited by package

- 100% avalanche tested
- Logic level threshold



DPAK

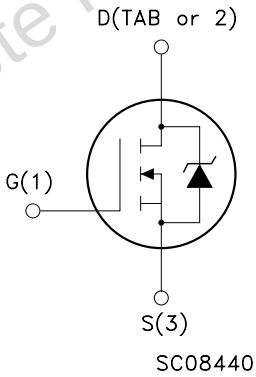


IPAK

Description

This MOSFET is the latest refinement of STMicroelectronic unique “Single Feature Size™” stripbased process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics, low gate charge and less critical aligment steps therefore a remarkable manufacturing reproducibility. This new improved device has been specifically designed for Automotive application and DC-DC converters.

Internal schematic diagram



Applications

- Switching application

Obsolete Product(s) - Obsolete Product(s)

Order codes

Part number	Marking	Package	Packaging
STD100N03LT4	D100N03L	DPAK	Tape & reel
STD100N03L-1	D100N03L-1	IPAK	Tube

Contents

1 Electrical ratings 3

2 Electrical characteristics 4

2.1 Electrical characteristics (curves) 6

3 Test circuit 9

4 Package mechanical data 10

5 Packaging mechanical data 13

6 Revision history 14

Obsolete Product(s) - Obsolete Product(s)

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (V_{GS} = 0)	30	V
V_{DGR}	Drain-gate voltage	± 20	V
I_D (1)	Drain current (continuous) at T_C = 25°C	80	A
I_D	Drain current (continuous) at T_C=100°C	70	A
I_{DM} (2)	Drain current (pulsed)	320	A
P_{TOT}	Total dissipation at T_C = 25°C	110	W
	Derating factor	0.73	W/°C
dv/dt (3)	Peak diode recovery voltage slope	3.9	V/ns
T_{stg}	Storage temperature	-55 to 175	°C
T_J	Max. operating junction temperature		

1. Current limited by package.
2. Pulse width limited by safe operating area
3. I_{SD} ≤80A, di/dt ≤360 A/µs, V_{DS} ≤$V_{(BR)DSS}$, T_J ≤T_{JMAX}

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case Max	1.36	°C/W
R_{thJA}	Thermal resistance junction-ambient Max	100	°C/W
T_l	Maximum lead temperature for soldering purpose	275	°C

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Not-repetitive avalanche current (pulse width limited by T_J max)	40	A
E_{AS}	Single pulsed avalanche energy (starting T_J = 25°C, I_D = I_{AV}, V_{DD} = 24V	500	mJ

Obsolete Product(s) - Obsolete Product(s)

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 250µA, V_{GS} = 0	30			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = Max rating, V_{DS} = Max rating @125°C			1 10	µA µA
I_{GSS}	Gate body leakage current (V_{DS} = 0)	V_{GS} = ±20V			±200	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS}= V_{GS}, I_D = 250µA	1			V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS} = 10V, I_D = 40A V_{GS} = 5V, I_D = 20A		0.0045 0.008	0.0055 0.01	Ω Ω
		V_{GS} = 10 V, I_D = 40 A @125°C V_{GS} = 5 V, I_D = 20 A @125°C		0.0068 0.0146		Ω Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	V_{DS} = 10 V, I_D = 15A		31		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		2060 728 67		pF pF pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 24V, I_D = 80A V_{GS} = 5V *Figure 15 on page 9*		20 7 7.5	27	nC nC nC
R_G	Gate input resistance	f = 1MHz gate DC Bias = 0 Test signal level = 20mV Open drain		1.9		Ω

1. Pulsed: pulse duration=300µs, duty cycle 1.5%

Obsolete Product(s) - Obsolete Product(s)

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD}= 15V, I_D= 40A, R_G=4.7Ω, V_{GS}=10V *Figure 14 on page 9*		9 205 31 35		ns ns ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				80	A
I_{SDM}(1)	Source-drain current (pulsed)				320	A
V_{SD}(2)	Forward on voltage	I_{SD} = 40A, V_{GS} = 0			1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 80A, di/dt = 100A/µs, V_{DD} = 25V, T_J = 150°C *Figure 16 on page 9*		40 40 2		ns µC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300µs, duty cycle 1.5%

Obsolete Product(s) - Obsolete Product(s)

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

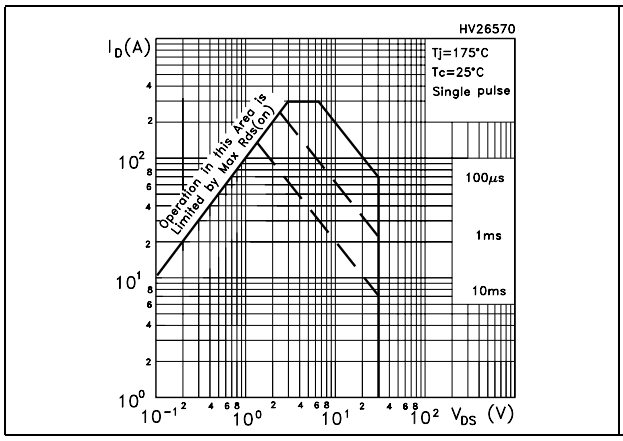


Figure 2. Thermal impedance

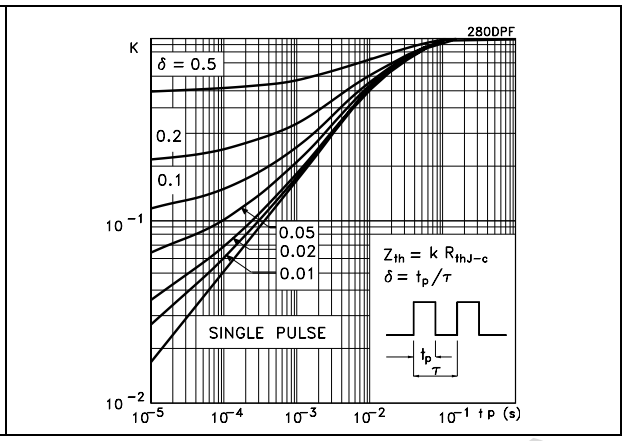


Figure 3. Output characterisics

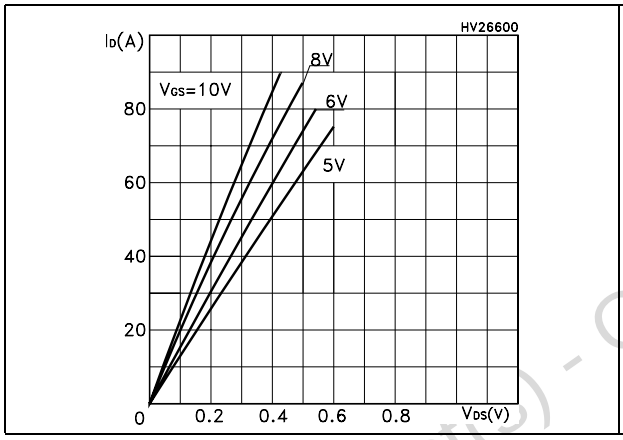


Figure 4. Transfer characteristics

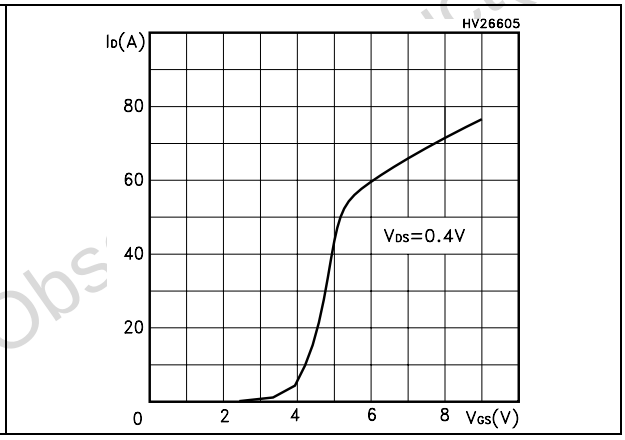


Figure 5. Transconductance

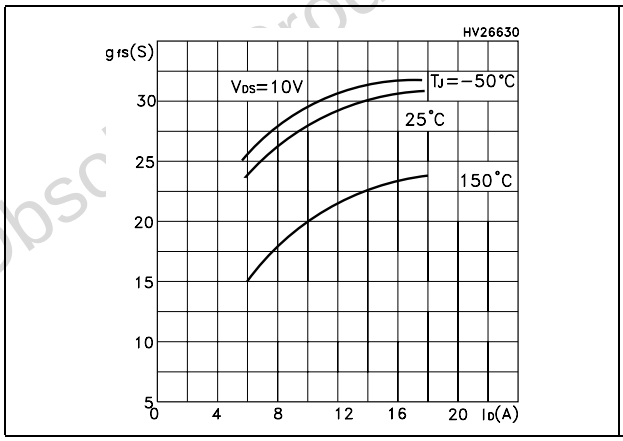
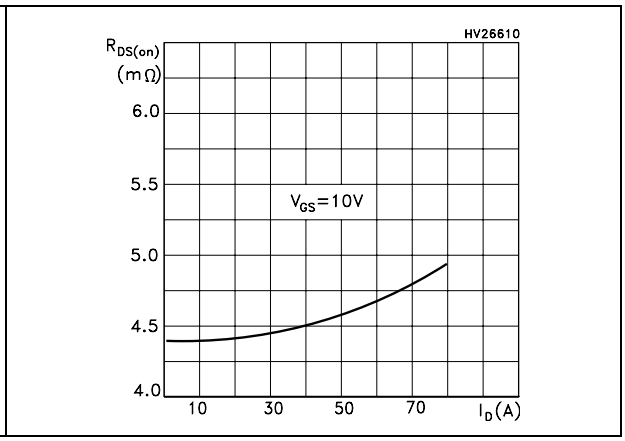


Figure 6. Static drain-source on resistance



Obsolete Product(s) - Obsolete Product(s)

Figure 7. Gate charge vs gate-source voltage

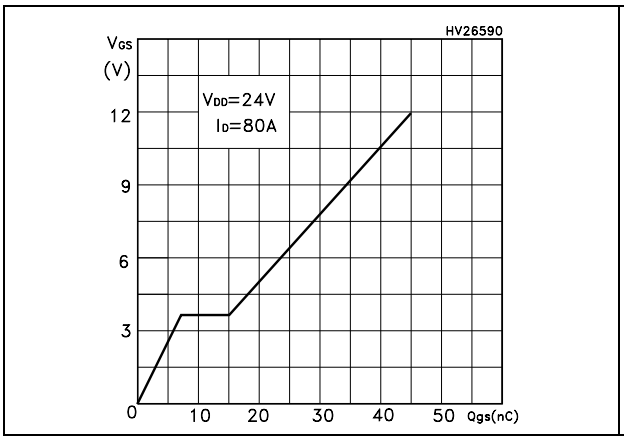


Figure 8. Capacitance variations

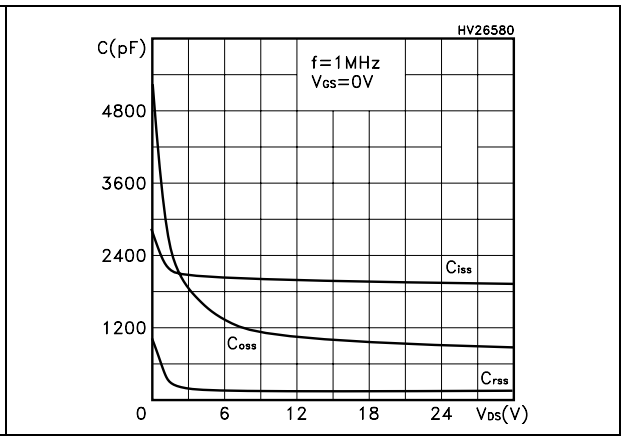


Figure 9. Normalized gate threshold voltage vs temperature

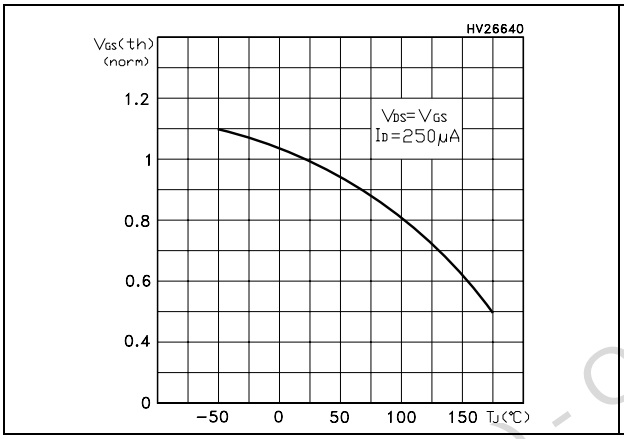


Figure 10. Normalized BVDSS vs temperature

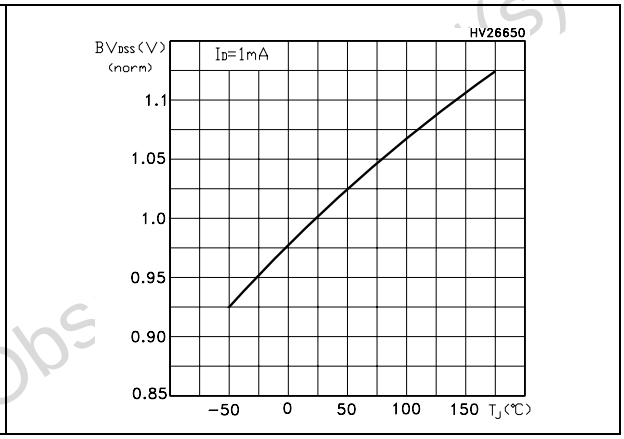


Figure 11. Normalized on resistance vs temperature

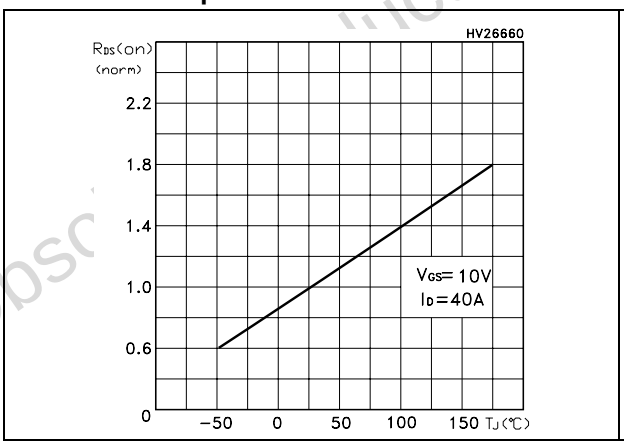


Figure 12. Source-drain diode forward characteristics

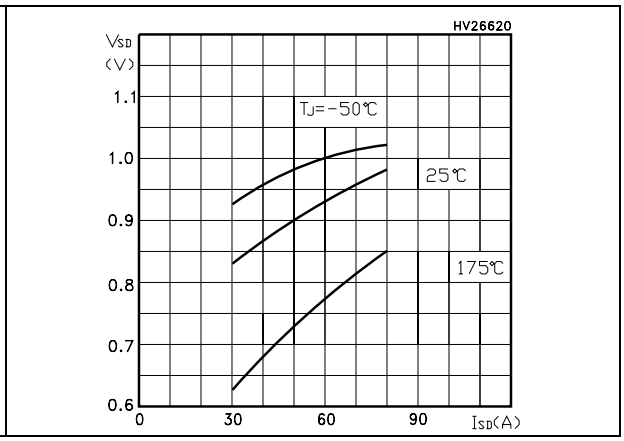
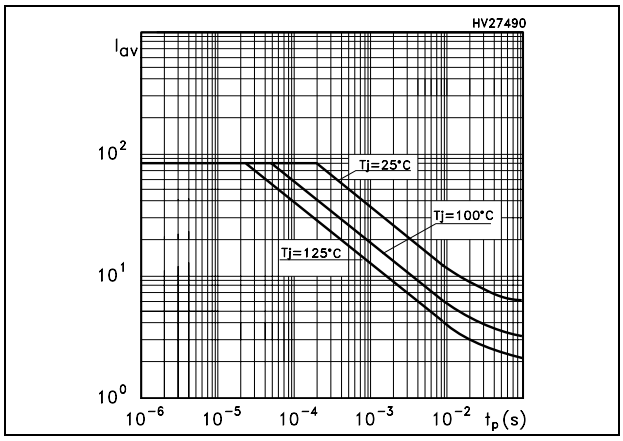


Figure 13. Allowable Iav vs time in avalanche



The previous curve gives the single pulse safe operating area for unclamped inductive loads, under the following conditions:

$P_{D(AVE)} = 0.5 * (1.3 * BV_{DSS} * I_{AV})$

$E_{AS(AR)} = P_{D(AVE)} * t_{AV}$

Where:

$_{IAV}$ is the Allowable Current in Avalanche

$P_{D(AVE)}$ is the Average Power Dissipation in Avalanche (Single Pulse)

t_{AV} is the Time in Avalanche

Obsolete Product(s) - Obsolete Product(s)

3 Test circuit

Figure 14. Switching times test circuit for resistive load

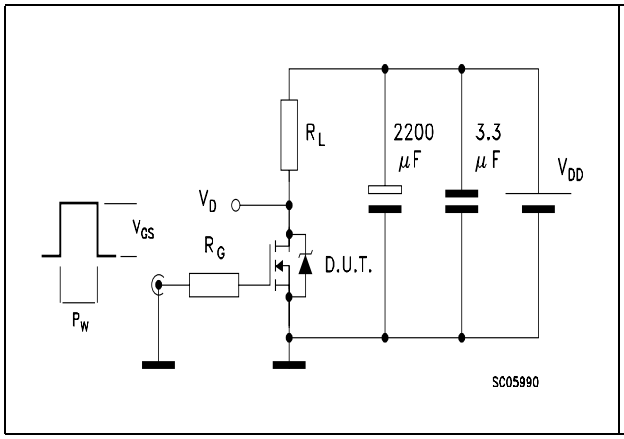


Figure 15. Gate charge test circuit

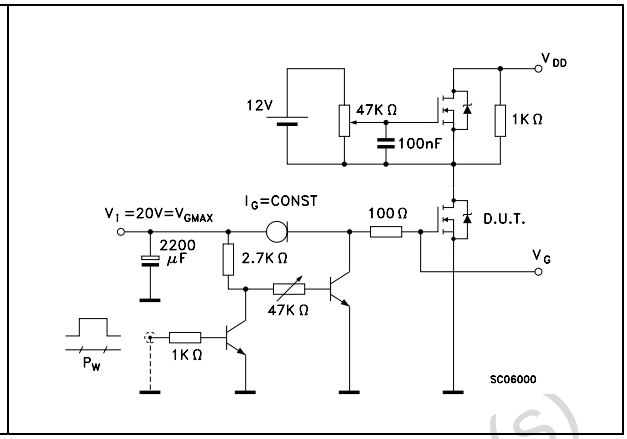
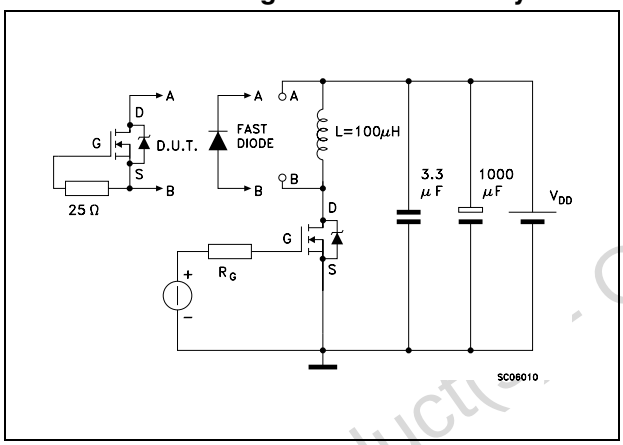


Figure 16. Test circuit for inductive load switching and diode recovery times



Obsolete Product(s) - Obsolete Product(s)

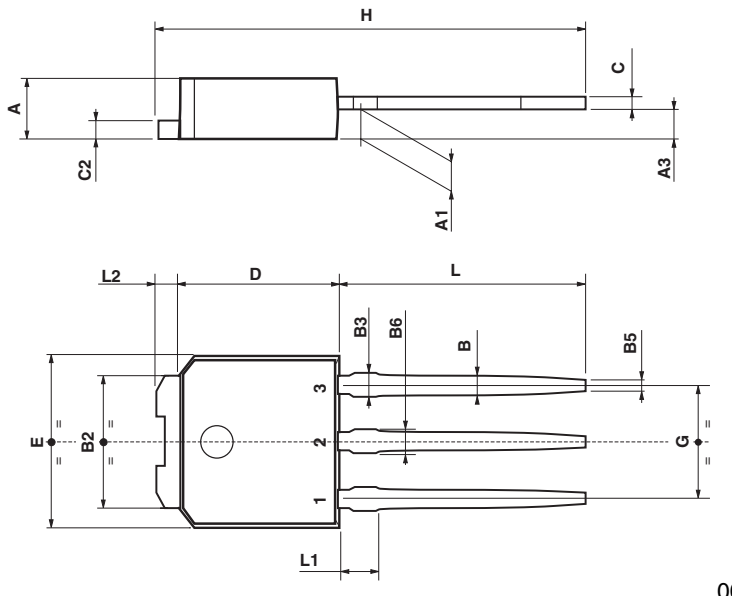
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Obsolete Product(s) - Obsolete Product(s)

TO-251 (IPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039

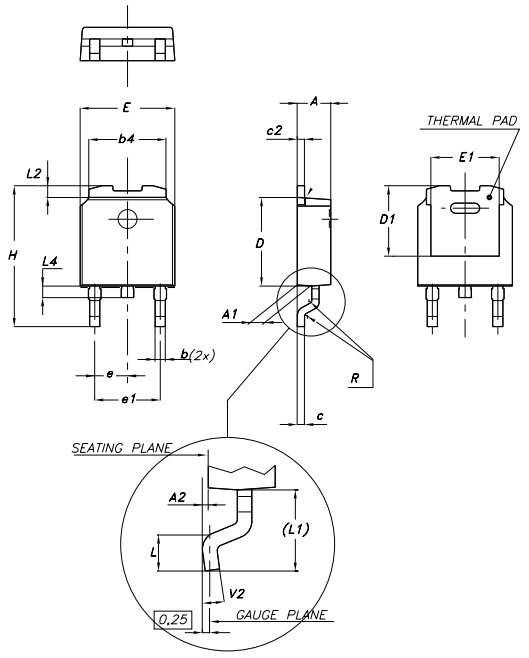


0068771-E

Obsole

DPAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
E	6.4		6.6	0.252		0.260
E1		4.7			0.185	
e		2.28			0.090	
e1	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°

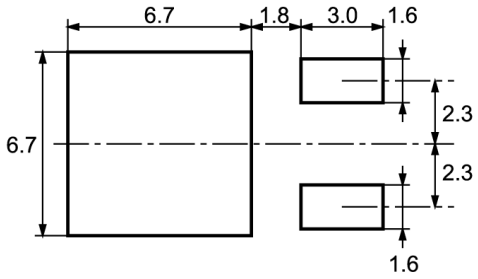


0068772-F

Obsole

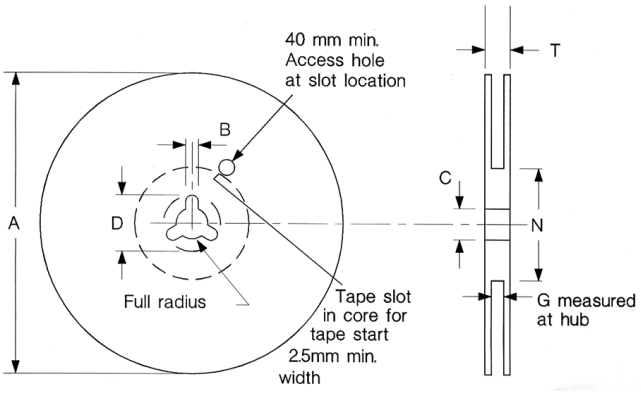
5 Packaging mechanical data

DPAK FOOTPRINT



All dimensions are in millimeters

TAPE AND REEL SHIPMENT



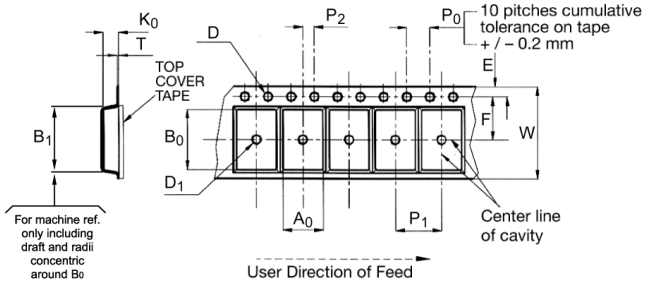
REEL MECHANICAL DATA

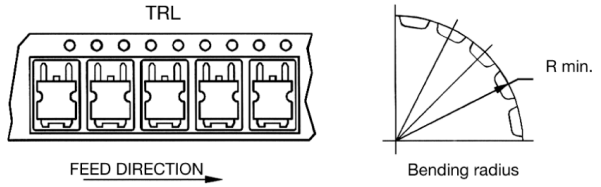
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY	BULK QTY
2500	2500

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641





6 Revision history

Table 8. Revision history

Date	Revision	Changes
15-Sep-2005	1	Initial release.
14-Sep-2005	2	Value changed on *Figure 1*
08-Aug-2006	3	New template, no content change

Obsolete Product(s) - Obsolete Product(s)

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